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(FILE 'HOME' ENTERED AT 13:56:07 ON 21 APR 2003)

FILE 'USPATFULL' ENTERED AT 13:56:19 ON 21 APR 2003

SET ABBREV ON

SET PLURAL ON

L1 60460 S (CHEMICAL ADJ3 VAPOR ADJ3 DEPOSITON OR CMP OR CHEMICAL ADJ3
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L2 60531 S (CHEMICAL ADJ3 VAPOR ADJ3 DEPOSITION OR CMP OR CHEMICAL
ADJ3
L3 60943 S (CHEMICAL VAPOR DEPOSITION OR CMP OR CHEMICAL MECHANICAL
POLI
L4 8267 S (HEAT OR HEATED OR HEATING OR VAPORIZ? OR VAPOUR?) (10A)
(CAR
L5 125 S L3 AND L4
L6 360551 S (REMOV? OR ELIMINAT? OR CLEAN? OR TREAT? OR STRIP? OR
ETCH?)
L7 4750 S L6 (P) L3
L8 5 S L7 AND L4
L9 628 S L6 (P) L4
L10 8 S L9 AND L3
L11 292729 S (CHEMICAL VAPOR DEPOSITION OR CMP OR CHEMICAL MECHANICAL
POLI
L12 20 S L9 AND L11
L13 63883 S L6 AND L11
L14 227 S L13 AND L4
L15 248264 S (CLEAN? OR TREAT? OR WASH? OR STERILIZ? OR ETCH? OR STRIP?)
(
L16 19317 S (HEAT OR HEATED OR HEATING OR VAPORIZ? OR VAPOUR?) (10A)
(PER
L17 71 S L15 (P) L16
L18 26 S (TRIFLUOROACETIC) (5A) (PERACID)

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1147	(clean or cleaning or cleaned or cleaner or cleanse or cleansed or cleanser or cleansed) with (chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition) with (chamber or equipment or container)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B; USOCR	2003/04/21 10:35
2	BRS	L2	343	(treat or treating or treated or treatment) with (chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition) with (chamber or equipment or container)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B; USOCR	2003/04/21 10:12
3	BRS	L3	384	(etch or etching or etched or etchant) with (chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition) with (chamber or equipment or container)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B; USOCR	2003/04/21 10:12
4	BRS	L4	13	(wash or washing or washed) with (chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition) with (chamber or equipment or container)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B; USOCR	2003/04/21 10:12

	Type	L #	Hits	Search Text	DBs	Time Stamp
5	BRS	L5	84	(clean or cleaning or cleaned or cleaner or cleanse or cleansed or cleanser or cleansed) same (inside or interior or interior adj3 wall or inner or inner adj3 wall) same ((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition) with (chamber or equipment or container))	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B; USOCR	2003/04/21 10:39
6	BRS	L6	84	(treat or treating or treated or treatment) same (inside or interior or interior adj3 wall or inner or inner adj3 wall) same ((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition) with (chamber or equipment or container))	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B; USOCR	2003/04/21 10:15
7	BRS	L7	7	(wash or washing or washed) same (inside or interior or interior adj3 wall or inner or inner adj3 wall) same ((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition) with (chamber or equipment or container))	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B; USOCR	2003/04/21 10:16

	Type	L #	Hits	Search Text	DBs	Time Stamp
8	BRS	L8	68	(etch or etching or etched or etchant) same (inside or interior or interior adj3 wall or inner or inner adj3 wall) same ((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition) with (chamber or equipment or container))	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B; USOCR	2003/04/21 10:16
9	BRS	L9	15	(strip or stripping or stripped or stripper) same (inside or interior or interior adj3 wall or inner or inner adj3 wall) same ((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition) with (chamber or equipment or container))	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B; USOCR	2003/04/21 10:16
10	BRS	L10	420518	carboxylic or polycarboxylic or dicarboxylic or trifluoroacetic or TFA or tri-fluoroacetic	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B; USOCR	2003/04/21 10:20
11	BRS	L11	1796	11 or 12 or 13 or 14 or 15 or 16 or 17 or 18 or 19	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B; USOCR	2003/04/21 10:20

	Type	L #	Hits	Search Text	DBs	Time Stamp
12	BRS	L12	2	111 same 110	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 10:34
13	BRS	L13	13	111 and 110	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 10:34
14	BRS	L14	1825	(clean or cleaning or cleaned or cleaner or cleanse or cleansed or cleanser or cleansed) with (chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP) with (chamber or equipment or container or apparatus)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 10:37
15	BRS	L15	527	(treat or treating or treated or treatment) with (chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP) with (chamber or equipment or container or apparatus)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 10:37

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	40	(wash or washing or washed) with (chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP) with (chamber or equipment or container or apparatus)	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 10:38
17	BRS	L17	527	(treat or treating or treated or treatment) with (chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP) with (chamber or equipment or container or apparatus)	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 10:38
18	BRS	L18	912	(etch or etching or etched or etchant) with (chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP) with (chamber or equipment or container or apparatus)	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 10:38
19	BRS	L19	105	(strip or stripping or stripped or stripper) with (chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP) with (chamber or equipment or container or apparatus)	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 10:38

	Type	L #	Hits	Search Text	DBs	Time Stamp
20	BRS	L20	115	(clean or cleaning or cleaned or cleaner or cleanse or cleansed or cleanser or cleansed) same (inside or interior or interior adj3 wall or inner or inner adj3 wall) same ((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP) with (chamber or equipment or container or apparatus))	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B; USOCR	2003/04/21 10:40
21	BRS	L21	100	(treat or treating or treated or treatment) same (inside or interior or interior adj3 wall or inner or inner adj3 wall) same ((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP) with (chamber or equipment or container or apparatus))	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B; USOCR	2003/04/21 10:41
22	BRS	L22	99	(etch or etching or etched or etchant) same (inside or interior or interior adj3 wall or inner or inner adj3 wall) same ((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP) with (chamber or equipment or container or apparatus))	USPAT; US-PGP; UB; EPO; JPO; DERWEN; T; IBM_TD; B; USOCR	2003/04/21 11:12

	Type	L #	Hits	Search Text	DBs	Time Stamp
23	BRS	L23	11	(wash or washing or washed) same (inside or interior or interior adj3 wall or inner or inner adj3 wall) same ((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP) with (chamber or equipment or container or apparatus))	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B; USOCR	2003/04/21 10:45
24	BRS	L24	26	(strip or stripping or stripper or stripped) same (inside or interior or interior adj3 wall or inner or inner adj3 wall) same ((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP) with (chamber or equipment or container or apparatus))	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B; USOCR	2003/04/21 11:09
25	BRS	L25	242116	(remove or removing or removed or removal) with (residue or residual or contaminant or impurity or particle or film or metal adj oxide or copper adj oxide)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B; USOCR	2003/04/21 10:43
26	BRS	L26	36401	(eliminate or eliminating or eliminated or elimination) with (residue or residual or contaminant or impurity or particle or film or metal adj oxide or copper adj oxide)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD; B; USOCR	2003/04/21 10:43

	Type	L #	Hits	Search Text	DBs	Time Stamp
27	BRS	L27	46863	(strip or stripping or stripped or stripper) with (residue or residual or contaminant or impurity or particle or film or metal adj oxide or copper adj oxide)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 10:44
28	BRS	L28	37522	(etch or etching or etched or etchant) with (residue or residual or contaminant or impurity or particle or film or metal adj oxide or copper adj oxide)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 10:44
29	BRS	L29	64570	(clean or cleaning or cleaned or cleanse or cleansing or cleansed) with (residue or residual or contaminant or impurity or particle or film or metal adj oxide or copper adj oxide)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:16
30	BRS	L30	692	(125 or 126 or 127 or 128 or 129) same ((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP) with (chamber or equipment or container or apparatus))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:30

	Type	L #	Hits	Search Text	DBs	Time Stamp
31	BRS	L31	0	(metal adj ligand adj complex\$3) and 130	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B; USOCR	2003/04/21 10:51
32	BRS	L32	0	(metal adj ligand adj complex\$3 or ligand adj complex\$3) and 130	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B; USOCR	2003/04/21 12:25
33	BRS	L33	1	(metal adj3 complex\$3) and 130	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B; USOCR	2003/04/21 10:55
34	BRS	L34	3193	111 or (114 or 115 or 116 or 117 or 118 or 119 or 120 or 121 or 122 or 123 or 124)	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B; USOCR	2003/04/21 11:09

	Type	L #	Hits	Search Text	DBs	Time Stamp
35	BRS	L35	218	134 and (cleaning adj3 (gas or vapour or gaseous or vapor))	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B; USOCR	2003/04/21 11:10
36	BRS	L36	255790	(134/\$ or 148/\$ or 510/\$ or 252/\$).ccls.	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B; USOCR	2003/04/21 11:11
37	BRS	L37	1	135 and 136	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B; USOCR	2003/04/21 11:11
38	BRS	L38	220	((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP or treatment) with (chamber or equipment or container or apparatus)) with (cleaning adj3 (gas or vapour or gaseous or vapor))	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B; USOCR	2003/04/21 12:17

	Type	L #	Hits	Search Text	DBs	Time Stamp
39	BRS	L39	1	138 and 136	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 11:54
40	BRS	L41	5372	kojima-y\$.in.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 11:59
41	BRS	L42	1999	oshima-y\$.in.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:15
42	BRS	L43	7368	141 or 142	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:15

	Type	L #	Hits	Search Text	DBs	Time Stamp
43	BRS	L44	362840	125 or 126 or 127 or 129 or 128	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:16
44	BRS	L45	19729	((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP or treatment) with (chamber or equipment or container or apparatus)) with (gas or gaseous or vapor or vapour or (cleaning adj3 (gas or vapour or gaseous or vapor)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:24
45	BRS	L46	1714	144 same 145	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:24
46	BRS	L47	21966	((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP or treatment) with (chamber or equipment or container or apparatus)) with (gas or gaseous or vapor or vapour or plasma or (cleaning adj3 (gas or vapour or gaseous or vapor)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:27

	Type	L #	Hits	Search Text	DBs	Time Stamp
47	BRS	L48	1862	147 same 144	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:25
48	BRS	L49	5	(metal adj ligand adj complex\$3 or ligand adj complex\$3 or metal adj complex\$3) and 148	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:32
49	BRS	L50	25579	((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP or treatment or deposition) with (chamber or equipment or container or apparatus)) with (gas or gaseous or vapor or vapour or plasma or (cleaning adj3 (gas or vapour or gaseous or vapor)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 13:02
50	BRS	L51	7551	(125 or 126 or 127 or 128 or 129) same ((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP or treatment or deposition) with (chamber or equipment or container or apparatus))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:45

	Type	L #	Hits	Search Text	DBs	Time Stamp
51	BRS	L53	10	152 and 136	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:33
52	BRS	L52	79	(metal adj3 ligand adj3 complex\$3 or ligand adj3 complex\$3 or metal adj3 complex\$3 or complexing or copper adj3 complex\$3) and 151	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:48
53	BRS	L54	14010	(125 or 126 or 127 or 128 or 129) and ((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP or treatment or deposition) with (chamber or equipment or container or apparatus))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:47
54	BRS	L55	163	(metal adj3 ligand adj3 complex\$3 or ligand adj3 complex\$3 or metal adj3 complex\$3 or complexing or copper adj3 complex\$3) and 154	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:55

	Type	L #	Hits	Search Text	DBs	Time Stamp
55	BRS	L56	27	155 and 136	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:49
56	BRS	L57	171	(metal adj3 ligand adj3 complex\$3 or ligand adj3 complex\$3 or metal adj3 complex\$3 or complexing or copper adj3 complex\$3 or chelate adj5 complex\$3 or chela\$5 adj5 complex\$3) and 154	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:57
57	BRS	L58	16023	(metal adj3 ligand adj3 complex\$3 or ligand adj3 complex\$3 or metal adj3 complex\$3 or complexing or copper adj3 complex\$3 or chelate adj5 complex\$3 or chela\$5 adj5 complex\$3) and 110	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 13:00
58	BRS	L59	34	157 AND L10	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:59

	Type	L #	Hits	Search Text	DBs	Time Stamp
59	BRS	L60	2	158 AND L43	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 12:59
60	BRS	L62	1	((chemical adj vapor adj deposition or vapor adj deposition or CVD or CMP or chemical adj mechanical adj polishing or PVD or physical adj vapor adj deposition or post-CMP or treatment or deposition) with (chamber or equipment or container or apparatus)) and 161	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 13:03
61	BRS	L63	7	161 and 136	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 13:07
62	BRS	L61	136	(metal adj3 ligand adj3 complex\$3 or ligand adj3 complex\$3 or metal adj3 complex\$3 or complexing or copper adj3 complex\$3 or chelate adj5 complex\$3 or chela\$5 adj5 complex\$3) and (trifluoroacetic or TFA or tri-fluoroacetic or trifluoro adj3 acetic)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 13:05

	Type	L #	Hits	Search Text	DBs	Time Stamp
63	BRS	L65	7	164 and 136	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 13:08
64	BRS	L64	172	(metal adj3 ligand adj3 complex\$3 or ligand adj3 complex\$3 or metal adj3 complex\$3 or complexing or copper adj3 complex\$3 or chelate adj5 complex\$3 or chela\$5 adj5 complex\$3) and (trifluoroacetic or TFA or tri-fluoroacetic or trifluoro adj3 acetic or "CF3COOH" or "CF.sub.3COOH")	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B; USOCR	2003/04/21 13:08

DERWENT-ACC-NO: 2000-148548

DERWENT-WEEK: 200027

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TITLE: Cleaning a CVD apparatus used for
depositing oxide
comprises contacting ceramics on semiconductor substrates
containing free the residues with an etching medium
diketones

INVENTOR: DEHM, C; FRITSCH, E ; WEINRICH, V ; WENDT, H

PATENT-ASSIGNEE: SIEMENS AG[SIEI]

PRIORITY-DATA: 1998DE-1033448 (July 24, 1998)

PATENT-FAMILY:

PUB-NO	PAGES	PUB-DATE	MAIN-IPC	
DE 19833448 A1	006	February 3, 2000	C23F 004/00	N/A
JP 2000096241 A	006	April 4, 2000	C23C 016/44	N/A

APPLICATION-DATA:

PUB-NO	APPL-DATE	APPL-DESCRIPTOR	APPL-NO
DE 19833448A1		N/A	
1998DE-1033448		July 24, 1998	
JP2000096241A		N/A	
1999JP-0206557		July 21, 1999	

INT-CL (IPC): C23C016/44, C23F004/00 , H01L021/205 ,
H01L021/3065

ABSTRACTED-PUB-NO: DE 19833448A

BASIC-ABSTRACT:

NOVELTY - Process for cleaning a CVD apparatus whose

process chamber is coated with alkali(ne earth) metal-containing process residues comprises contacting the residues with an etching medium containing free diketones and reacting the diketones with the process residues forming alkaline earth metal and metal complexes.

USE - For cleaning CVD apparatus used for depositing oxide ceramics on semiconductor substrates.

ADVANTAGE - The process is simple.

CHOSEN-DRAWING: Dwg.0/2

DERWENT-CLASS: A25 A26 A97 L03 M14 U11

CPI-CODES: A12-W12B; L04-D01; M14-A;

EPI-CODES: U11-A10; U11-C09B; U11-C09F;